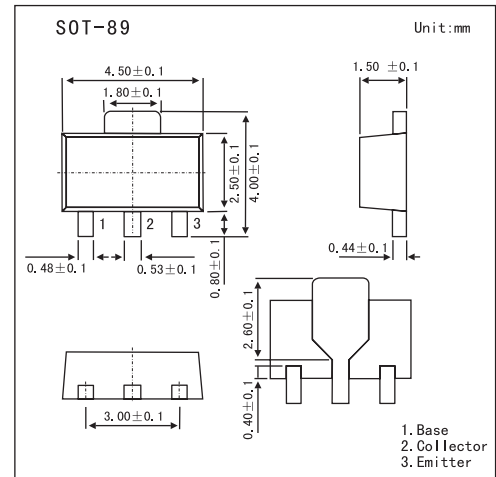


NPN Silicon Epitaxial Transistor

2SD1000

■ Features

- World standard miniature package:SOT-89.
- Low collector saturation voltage.

■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

Parameter	Symbol	Rating	Unit
Collector-base voltage	V_{CB0}	60	V
Collector-emitter voltage	V_{CE0}	50	V
Emitter-base voltage	V_{EB0}	5	V
Collector current (DC)	I_C	0.7	A
Collector Current (pulse) *	I_C	1.0	A
Total power dissipation	P_T	2.0	W
Junction temperature	T_j	150	$^\circ\text{C}$
Storage temperature	T_{stg}	-55 to +150	$^\circ\text{C}$

* Pulse Test $PW \leq 10\text{ms}$, Duty Cycle $\leq 50\%$.

■ Electrical Characteristics $T_a = 25^\circ\text{C}$

Parameter	Symbol	Testconditions	Min	Typ	Max	Unit
Collector cutoff current	I_{CB0}	$V_{CB} = 60\text{ V}, I_E = 0\text{ A}$			100	nA
Emitter cutoff current	I_{EB0}	$V_{EB} = 5.0\text{ V}, I_C = 0\text{ A}$			100	nA
DC current gain *	hFE	$V_{CE} = 1.0\text{ V}, I_C = 100\text{ mA}$	90	200	400	
		$V_{CE} = 1.0\text{ V}, I_C = 500\text{ mA}$	50	150		
Collector saturation voltage *	$V_{CE(sat)}$	$I_C = 500\text{ mA}, I_B = 50\text{ mA}$		0.12	0.4	V
Base saturation voltage *	$V_{BE(sat)}$	$I_C = 500\text{ mA}, I_B = 50\text{ mA}$		0.9	1.2	V
Base-emitter voltage *	V_{BE}	$V_{CE} = 6.0\text{ V}, I_C = 10\text{ mA}$	600	635	700	mV
Gain bandwidth product	f _T	$V_{CE} = 6.0\text{ V}, I_E = -10\text{ mA}$		110		MHz
Output capacitance	C_{ob}	$V_{CB} = 6\text{ V}, I_E = 0, f = 1.0\text{ MHz}$		13		pF

* Pulsed: $PW \leq 350\ \mu\text{s}$, duty cycle $\leq 2\%$

■ hFE Classification

Marking	LM	LL	LK
hFE	90~180	135~270	200~400